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Överspänningsskydd för lågspänning – Del 341: Tyristoravledare (TSS) – Prestanda och provningsmetoder

*Components for low-voltage surge protection –
Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)*

Som svensk standard gäller europastandarden EN IEC 61643-341:2020. Den svenska standarden innehåller den officiella engelska språkversionen av EN IEC 61643-341:2020.

Nationellt förord

Europastandarden EN IEC 61643-341:2020

består av:

- **europastandardens ikraftsättningsdokument**, utarbetat inom CENELEC
- **IEC 61643-341, Second edition, 2020 - Components for low-voltage surge protection - Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)**

utarbetad inom International Electrotechnical Commission, IEC.

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**Components for low-voltage surge protection - Part 341:
Performance requirements and test circuits for thyristor surge
suppressors (TSS)
(IEC 61643-341:2020)**

Composants pour parafoudres basse tension - Partie 341:
Exigences de performance et circuits d'essai pour
parafoudres à thyristor (TSS)
(IEC 61643-341:2020)

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Niederspannung - Teil 341: Leistungsanforderungen sowie
Prüfschaltungen für Suppressordioden (TSS)
(IEC 61643-341:2020)

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Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

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SS-EN IEC 61643-341, utg 2:2020

European foreword

The text of document 37B/218/FDIS, future edition 2 of IEC 61643-341, prepared by SC 37B "Components for low-voltage surge protection" of IEC/TC 37 "Surge arresters" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 61643-341:2020.

The following dates are fixed:

- latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2021-03-17
- latest date by which the national standards conflicting with the document have to be withdrawn (dow) 2023-06-17

This document supersedes EN 61643-341:2001 and all of its amendments and corrigenda (if any).

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The text of the International Standard IEC 61643-341:2020 was approved by CENELEC as a European Standard without any modification.

In the official version, for Bibliography, the following notes have to be added for the standards indicated:

IEC 60060-1:2010	NOTE	Harmonized as EN 60060-1:2010 (not modified)
IEC 60068-2-20:2008	NOTE	Harmonized as EN 60068-2-20:2008 (not modified)
IEC 60068-2-21:2006	NOTE	Harmonized as EN 60068-2-21:2006 (not modified)
IEC 60099-4:2014	NOTE	Harmonized as EN 60099-4:2014 (not modified)
IEC 60721-3-3:2019	NOTE	Harmonized as EN IEC 60721-3-3:2019 (not modified)
IEC 60721-3-9:1993	NOTE	Harmonized as EN 60721-3-9:1993 (not modified)
IEC 60749-1:2002	NOTE	Harmonized as EN 60749-1:2003 (not modified)
IEC 60950-1:2005	NOTE	Harmonized as EN 60950-1:2006 (modified)
IEC 61000-4-5:2014	NOTE	Harmonized as EN 61000-4-5:2014 (not modified)
IEC 61643-11:2011	NOTE	Harmonized as EN 61643-11:2012 (modified)
IEC 62475:2010	NOTE	Harmonized as EN 62475:2010 (not modified)

Annex ZA (normative)

Normative references to international publications with their corresponding European publications

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE 1 Where an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here: www.cenelec.eu.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 60050-521	-	International Electrotechnical Vocabulary - Part 521: Semiconductor devices and integrated circuits	-	-
IEC 60068-2-20	2008	Environmental testing - Part 2-20: Tests - Test T: Test methods for solderability and resistance to soldering heat of devices with leads	EN 60068-2-20	2008

CONTENTS

FOREWORD	6
1 Scope	8
2 Normative references	8
3 Terms, definitions, abbreviated terms and symbols	8
3.1 Parametric terms, letter symbols and definitions	9
3.2 General terms	9
3.3 Main terminal ratings	9
3.4 Main terminal characteristics	11
3.5 Additional and derived parameters	12
3.6 Temperature related parameters	12
3.7 Gate terminal parameters	13
3.8 Abbreviated terms	15
3.9 Circuit symbols	15
4 TSS types	16
5 Service conditions	18
5.1 Normal service conditions	18
5.2 Storage temperature range, T_{stgmin} to T_{stgmax}	18
6 Mechanical requirements and identification	18
6.1 Robustness of terminations	18
6.2 Solderability	18
6.3 Marking	18
6.4 Documentation	18
7 Standard test methods	19
7.1 Failure rates	19
7.2 Test conditions	19
7.2.1 General	19
7.2.2 Standard atmospheric conditions	19
7.2.3 Measurement errors	20
7.2.4 Measurement accuracy	20
7.2.5 Designated impulse shape and values	20
7.2.6 Multiple TSS	20
7.2.7 Gated TSS testing	20
7.3 Rating test procedures	20
7.3.1 General	20
7.3.2 Repetitive peak off-state voltage, V_{DRM}	21
7.3.3 Repetitive peak on-state current, I_{TRM}	21
7.3.4 Non-repetitive peak on-state current, I_{TSM}	22
7.3.5 Non-repetitive peak pulse current, I_{PP}	23
7.3.6 Repetitive peak reverse voltage, V_{RRM}	24
7.3.7 Non-repetitive surge forward current, I_{FSM}	24
7.3.8 Repetitive peak forward current, I_{FRM}	24
7.3.9 Critical rate of rise of on-state current, di/dt	25
7.4 Characteristic test procedures	26
7.4.1 General	26
7.4.2 Off-state current, I_D	26
7.4.3 Repetitive peak off-state current, I_{DRM}	27

7.4.4	Repetitive peak reverse current, I_{RRM}	27
7.4.5	Breakover voltage, $V_{(BO)}$ and current, $I_{(BO)}$	27
7.4.6	On-state voltage, V_T	29
7.4.7	Holding current, I_H	33
7.4.8	Off-state capacitance, C_O	34
7.4.9	Forward voltage, V_F	37
7.4.10	Peak forward recovery voltage, V_{FRM}	37
7.4.11	Critical rate of off-state voltage rise, dv/dt	38
7.4.12	Variation of holding current with temperature	38
7.4.13	Gate-to-adjacent terminal peak off-state voltage and peak off-state gate current, V_{GDM} , I_{GDM}	38
7.4.14	Gate reverse current, adjacent terminal open, I_{GAO} , I_{GKO}	39
7.4.15	Gate reverse current, main terminals short-circuited, I_{GAS} , I_{GKS}	40
Annex A (informative) Common impulse waveshapes		41
A.1	General.....	41
A.2	Types of impulse generator	41
A.3	Impulse generator parameters	41
A.3.1	Glossary of terms.....	41
A.3.2	Virtual parameters	42
A.4	Impulse generators typically used for surge protector testing	44
A.4.1	General.....	44
A.4.2	Impulse generators with a defined voltage waveform	44
A.4.3	Impulse generators with a defined current waveform.....	44
A.4.4	Generators with defined voltage and current waveforms	45
Annex B (informative) Glossary of IEC 60747-6 [10] thyristor terms		48
B.1	General.....	48
B.2	Thyristor types	48
B.3	Basic terms defining the static voltage-current characteristics of triode thyristors.....	49
B.4	Basic terms defining the static voltage-current characteristics of diode thyristors.....	51
B.5	Particulars of the static voltage-current characteristics of triode and diode thyristors.....	52
B.6	Terms related to ratings and characteristics; principal voltages.....	54
B.7	Terms related to ratings and characteristics; principal currents	55
B.8	Terms related to ratings and characteristics; gate voltages and currents.....	57
B.9	Terms related to ratings and characteristics; powers, energies and losses.....	59
B.10	Letter symbols	61
B.10.1	General.....	61
B.10.2	List of letter symbols.....	62
Annex C (informative) Additional parametric tests		64
C.1	General.....	64
C.2	Temperature derating.....	64
C.3	Thermal resistance, R_{th}	64
C.4	Transient thermal impedance, $Z_{th}(t)$	65
C.5	Gate reverse current, on-state, I_{GAT} , I_{GKT}	66
C.6	Gate reverse current, forward conducting state, I_{GAF} , I_{GKF}	67
C.7	Gate switching charge, Q_{GS}	68
C.8	Peak gate switching current, I_{GSM}	70

C.9	Gate-to-adjacent terminal breakover voltage, $V_{GK(BO)}$, $V_{GA(BO)}$	71
Annex D (normative)	Preferred values	72
D.1	General.....	72
D.2	$V_{(BO)}$ and V_{DRM}	72
D.3	C_O , V_{DRM} and I_{PP}	73
D.4	I_H	74
D.5	I_{PP} and time to half value (duration).....	74
	Bibliography.....	75
Figure 1	– Fixed voltage, two terminals: a) reverse blocking and b) reverse conducting	15
Figure 2	– Gated reverse blocking: a) P gate b) N gate and c) P & N gate	16
Figure 3	– Gated reverse conducting: a) P gate and b) N gate	16
Figure 4	– Bidirectional: a) 2 terminal fixed voltage and b) gated	16
Figure 5	– Switching quadrant characteristics: a) fixed-voltage TSS and b) gated TSS	17
Figure 6	– TSS non-switching characteristics: a) reverse blocking b) reverse conducting	17
Figure 7	– Test circuit for verifying repetitive peak off-state voltage (V_{DRM}).....	21
Figure 8	– Test circuit for verifying repetitive peak on-state current, I_{TRM}	21
Figure 9	– Repetitive peak on-state current waveforms.....	22
Figure 10	– Test circuit for verifying non-repetitive peak on-state current, I_{TSM}	23
Figure 11	– Test circuit for verifying non-repetitive peak pulse current, I_{PP}	24
Figure 12	– Test circuit for verifying critical rate of rise of on-state current (di/dt)	25
Figure 13	– Half sine-wave di/dt test circuit	26
Figure 14	– Test circuit for off-state current, I_D at V_D	27
Figure 15	– Test circuit for breakover, $V_{(BO)}$ and $I_{(BO)}$ and on-state voltage, V_T	28
Figure 16	– Voltage and current waveforms versus time for a fixed-voltage TSS showing switch-on, on-state and switch-off events	28
Figure 17	– Waveform expansions of Figure 16	30
Figure 18	– Voltage and current waveforms versus time for a gated TSS showing switch-on, on-state and switch-off events.....	31
Figure 19	– Waveform expansions of Figure 18	32
Figure 20	– Test circuit for holding current, I_H	33
Figure 21	– Test circuit for holding current with additional DC bias	34
Figure 22	– Test circuit for capacitance measurement	34
Figure 23	– Test circuit for capacitance measurement with external DC bias	35
Figure 24	– Test circuit for capacitance measurement of multi-terminal TSS.....	36
Figure 25	– Diode voltage and current waveforms versus time showing V_{FRM} and rising current di/dt	37
Figure 26	– Test circuit for exponential critical rate of off-state voltage rise, dv/dt	38
Figure 27	– Test circuit for gate-to-adjacent terminal peak off-state voltage and current, V_{GDM} and I_{GDM}	39
Figure 28	– Test circuit for gate reverse current, adjacent terminal open, I_{GAO} , I_{GKO}	39
Figure 29	– Test circuit for gate reverse current, main terminals short-circuited, I_{GAS} , I_{GKS}	40
Figure A.1	– Current or voltage impulse amplitude versus time showing a 10 % to 90 % T_1 front time and T_2 time to half value	43

Figure A.2 – Voltage impulse amplitude versus time showing a 30 % to 90 % T_1 front time and T_2 time to half value	43
Figure B.1 – Particulars of the static characteristic of unidirectional thyristors	52
Figure B.2 – Particulars of the static characteristic of bidirectional thyristors	53
Figure B.3 – a) Approximation of the on-state V_T - I_T characteristic b) Approximation of the reverse V_R - I_R characteristic	60
Figure C.1 – Test circuit for thermal resistance and impedance	65
Figure C.2 – Thermal impedance versus time	66
Figure C.3 – Test circuit for gate reverse current, on-state, I_{GAT} , I_{GKT}	67
Figure C.4 – Test circuit for gate reverse current, forward conducting state, I_{GAF} , I_{GKF}	68
Figure C.5 – Test circuit for gate switching current, gate switching charge and gate-to-adjacent terminal breakover voltage, I_{GSM} , Q_{GS} , $V_{GK(BO)}$, $V_{GA(BO)}$	69
Figure C.6 – Test circuit of an integrated gate diode TSS for gate switching current, gate switching charge and gate-to-adjacent terminal breakover voltage I_{GSM} , Q_{GS} , $V_{GK(BO)}$, $V_{GA(BO)}$	70
Figure C.7 – Overall and expanded clamping waveforms for a P-type gate TSS showing $V_{GK(BO)}$ and Q_{GS} measurement ($di_K/dt = 10 \text{ A}/\mu\text{s}$, $V_{GG} = -72 \text{ V}$)	71
Figure D.1 – $V_{(BO)}/V_{DRM}$ ratio against V_{DRM}	72
Figure D.2 – $V_{(BO)}$ vs V_{DRM}	73
Figure D.3 – Capacitance variation with DC bias	73
Figure D.4 – I_{PP} versus Duration for various 10/1 000 current ratings	74
Table 1 – Types of TSS	17
Table 2 – Breakover ramp rate test values	29
Table A.1 – Voltage impulse generators	44
Table A.2 – Current impulse generators	45
Table A.3 – Voltage and current impulse generators	46
Table A.4 – Other voltage and current impulse generators	47
Table B.1 – Additional general subscripts	61
Table B.2 – Principal voltages, anode-cathode voltages	62
Table B.3 – Principal currents, anode currents, cathode currents	62
Table B.4 – Gate voltages	63
Table B.5 – Gate currents	63
Table B.6 – Sundry quantities	63
Table B.7 – Power loss	63

INTERNATIONAL ELECTROTECHNICAL COMMISSION

COMPONENTS FOR LOW-VOLTAGE SURGE PROTECTION –

Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)

FOREWORD

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International Standard IEC 61643-341 has been prepared by subcommittee 37B, Components for low-voltage surge protection, of IEC technical committee 37: Surge arresters.

This second edition of IEC 61643-341 cancels and replaces the first edition published in 2001. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition: Addition of performance values.

The text of this standard is based on the following documents:

FDIS	Report on voting
37B/218/FDIS	37B/220/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of IEC 61643 series, under the general title *Components for low-voltage surge protective devices*, can be found on the IEC website.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

COMPONENTS FOR LOW-VOLTAGE SURGE PROTECTION –

Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)

1 Scope

This part of IEC 61643 specifies standard test circuits and methods for thyristor surge suppressor (TSS) components. These surge protective components, SPCs, are specially formulated thyristors designed to limit overvoltages and divert surge currents by clamping and switching actions. These SPCs are used in the construction of surge protective devices (SPDs) and equipment used in Information & Communications Technologies (ICT) networks with voltages up to AC 1 000 V and DC 1 500 V. This document is applicable to gated or non-gated TSS components with third quadrant (-v and -i) characteristics of blocking, conducting or switching.

This document contains information on

- terminology;
- letter symbols;
- essential ratings and characteristics;
- rating verification and characteristic measurement;

This document does not apply to the conventional three-terminal thyristors as covered by IEC 60747-6.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60050-521, *International Electrotechnical Vocabulary – Chapter 521: Semiconductor devices and integrated circuits*

IEC 60068-2-20:2008, *Environmental testing – Part 2-20: Tests – Test T: Test methods for solderability and resistance to soldering heat of devices with leads*